

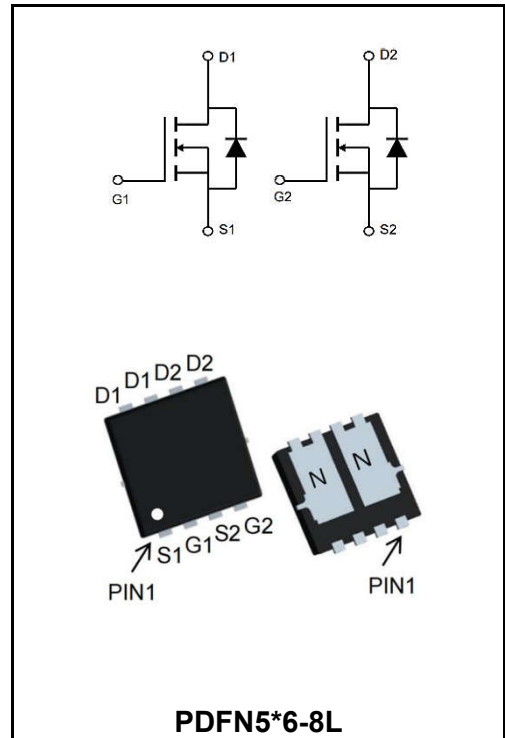
**60V N+N-CHANNEL ENHANCEMENT MODE MOSFET**

**MAIN CHARACTERISTICS**

<b>I<sub>D</sub></b>	50A
<b>V<sub>DSS</sub></b>	60V
<b>R<sub>DS(on)-typ(@V<sub>GS</sub>=10V)</sub></b>	< 16mΩ( <b>Type:11 mΩ</b> )

**Application**

- ◆ Battery protection
- ◆ Load switch
- ◆ Uninterruptible power supply



**Product Specification Classification**

Part Number	Package	Marking	Pack
YFW50H06NF	PDFN5*6-8L	YFW 50H06NF XXXXX	5000PCS/Tape

**Maximum Ratings at Tc=25°C unless otherwise specified**

Characteristics	Symbols	Value	Units
Drain-Source Voltage	<b>V<sub>DS</sub></b>	60	<b>V</b>
Gate - Source Voltage	<b>V<sub>GS</sub></b>	±20	<b>V</b>
Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup> @T <sub>A</sub> =25°C	<b>I<sub>D</sub></b>	50	<b>A</b>
Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup> @T <sub>A</sub> =70°C	<b>I<sub>D</sub></b>	25	<b>A</b>
Pulsed Drain Current <sup>2</sup>	<b>I<sub>DM</sub></b>	150	<b>A</b>
Single Pulse Avalanche Energy <sup>3</sup>	<b>E<sub>AS</sub></b>	64	<b>mJ</b>
Total Power Dissipation <sup>4</sup> @T <sub>A</sub> =25°C	<b>P<sub>D</sub></b>	3.6	<b>W</b>
Storage Temperature Range	<b>T<sub>STG</sub></b>	-55 to +150	<b>°C</b>
Operating Junction Temperature Range	<b>T<sub>J</sub></b>	-55 to +150	<b>°C</b>
Thermal Resistance Junction-Case <sup>1</sup>	<b>R<sub>θJC</sub></b>	2.8	<b>°C/W</b>
Thermal Resistance Junction-Ambient <sup>1</sup>	<b>R<sub>θJA</sub></b>	25	<b>°C/W</b>

**Maximum Ratings at Tc=25°C unless otherwise specified**

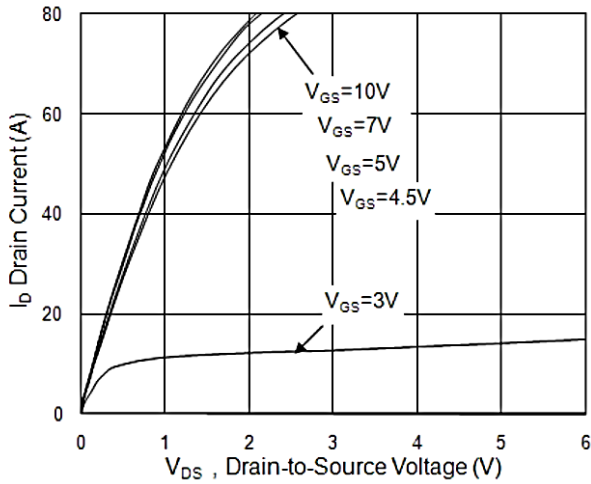
Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	$B_{VDSS}$	60	65	-	V
BVDSS Temperature Coefficient	Reference to 25°C, $I_D=1mA$	$\Delta B_{VDSS}/\Delta T_J$	-	0.057	-	V/°C
Static Drain-Source On-Resistance <sup>2</sup>	$V_{GS}=10V, I_D=12A$	$R_{DS(ON)}$	-	11	16	mΩ
	$V_{GS}=4.5V, I_D=10A$		-	15	20	
Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	$V_{GS(th)}$	1.2	1.6	2.5	V
$V_{GS(th)}$ Temperature Coefficient		$\Delta V_{GS(th)}$	-	-5.68	-	mV/°C
Drain-Source Leakage Current	$V_{DS}=48V, V_{GS}=0V, T_J=25^\circ C$	$I_{DSS}$	-	-	1	uA
	$V_{DS}=48V, V_{GS}=0V, T_J=55^\circ C$		-	-	5	
Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	$I_{GSS}$	-	-	±100	nA
Forward Transconductance	$V_{DS} = 5V, I_D = 15A$	$g_{fs}$	-	45	-	S
Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1MHz$	$R_g$	-	1.7	-	Ω
Total Gate Charge ( 4.5V )	$V_{DS}=48V$ $V_{GS}=4.5V$ $I_D=15A$	$Q_g$	-	19.3	-	nC
Gate-Source Charge		$Q_{gs}$	-	7.1	-	
Gate-Drain Charge		$Q_{gd}$	-	7.6	-	
Turn-on delay time	$V_{DD} = 30V$ $V_{GS} = 10V$ $R_G = 3.3\Omega$ $I_D = 15A$	$t_{d(on)}$	-	7.2	-	ns
Rise Time		$T_r$	-	50	-	
Turn-Off Delay Time		$t_{d(OFF)}$	-	36.4	-	
Fall Time		$t_f$	-	7.6	-	
Input Capacitance	$V_{DS}=15V$ $V_{GS}=0V$ $f=1.0MHz$	$C_{iss}$	-	2423	-	pF
Output Capacitance		$C_{oss}$	-	145	-	
Reverse Transfer Capacitance		$C_{rss}$	-	97	-	
Continuous Source Current <sup>1,5</sup>	$V_G=V_D=0V, \text{Force Current}$	$I_S$	-	-	35	A
Pulsed Source Current <sup>2,5</sup>		$I_{SM}$	-	-	80	A
Diode Forward Voltage <sup>2</sup>	$V_{GS}=0V, I_S=1A, T_J=25^\circ C$	$V_{SD}$	-	-	1	V
Reverse Recovery Time	$I_F=15A,$ $di/dt=100A/\mu s, T_J=25^\circ C$	$t_{rr}$	-	16.3	-	nS
Reverse Recovery Charge		$Q_{rr}$	-	11	-	nC

Note :

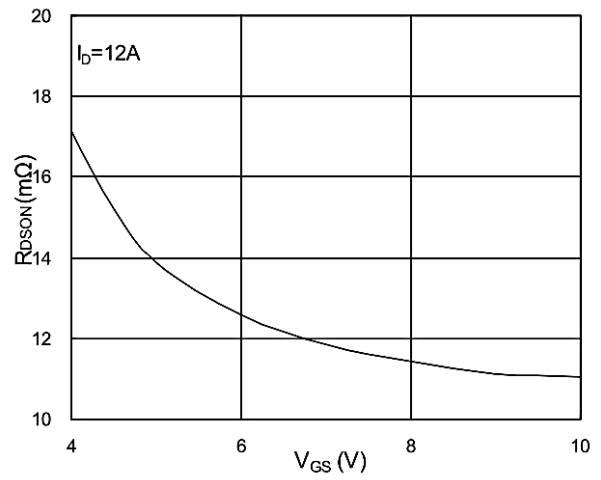
- 1、 The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、 The data tested by pulsed , pulse width  $\cong 300\mu s$  , duty cycle  $\cong 2\%$
- 3、 The power dissipation is limited by 150°C junction temperature
- 4、 The EAS data shows Max. rating . The test condition is  $V_{DD}=48V, V_{GS}=10V, L=0.1mH, I_{AS}=25A$ , starting  $T_J=25^\circ C$
- 5、 The data is theoretically the same as  $I_D$  and  $I_{DM}$  , in real applications , should be limited by total power dissipation.

**Ratings and Characteristic Curves**

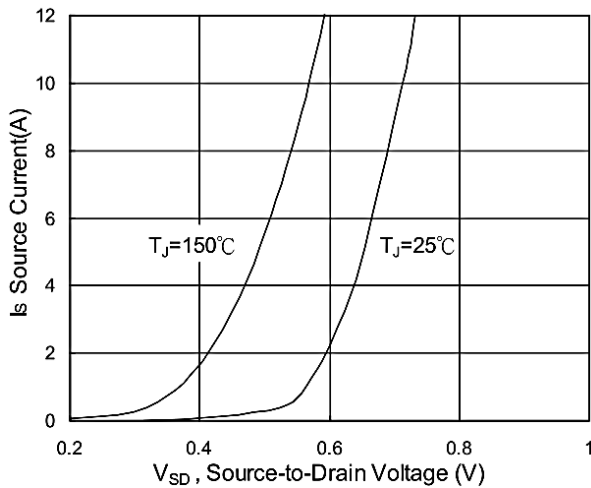
**Typical Characteristics**



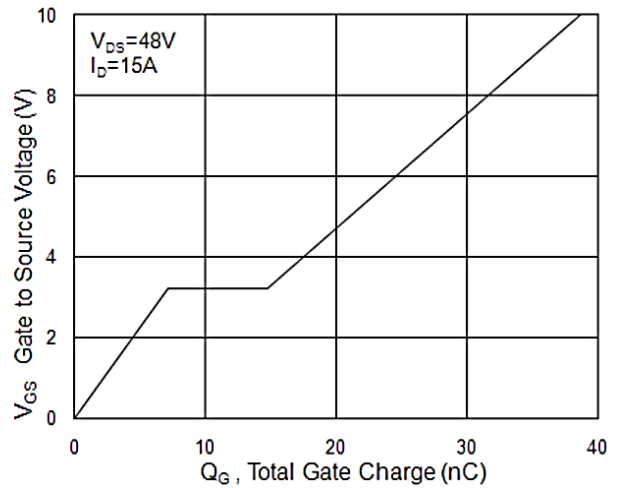
**Fig.1 Typical Output Characteristics**



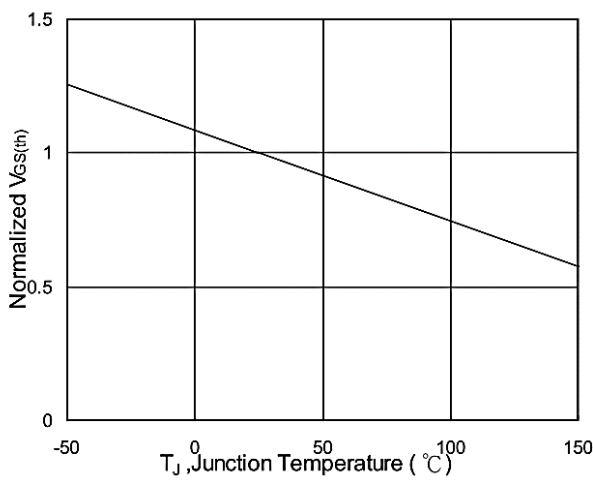
**Fig.2 On-Resistance v.s Gate-Source**



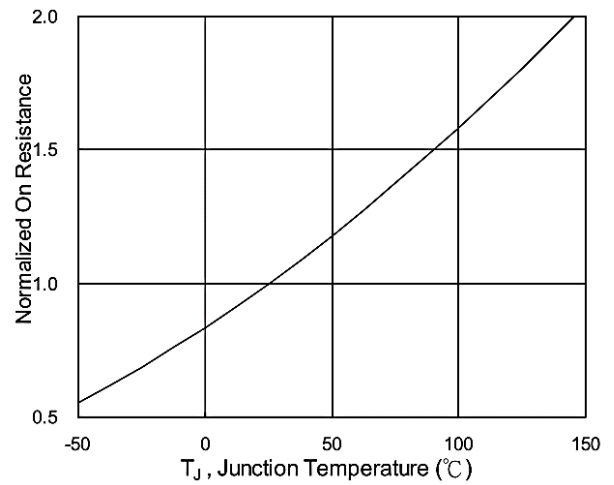
**Fig.3 Forward Characteristics of Reverse**



**Fig.4 Gate-Charge Characteristics**

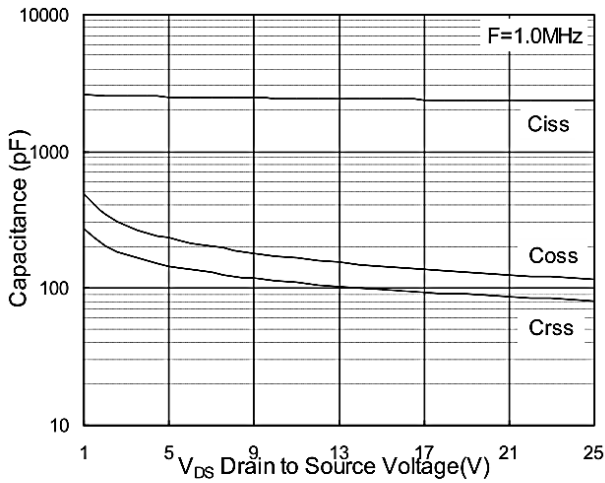


**Fig.5 Normalized  $V_{GS}$  v.s  $T_J$**

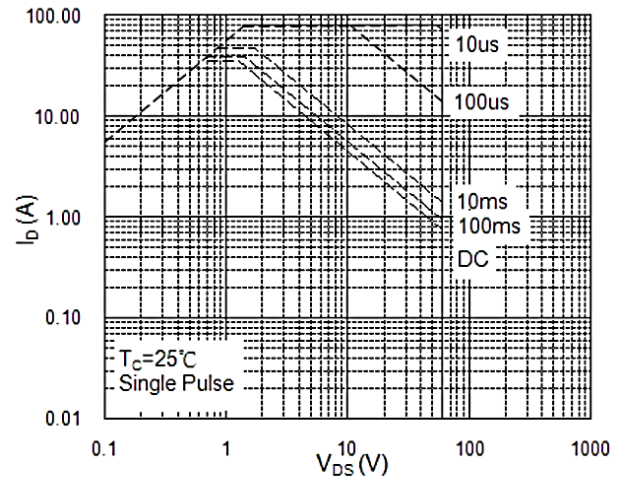


**Fig.6 Normalized  $R_{DS(on)}$  v.s  $T_J$**

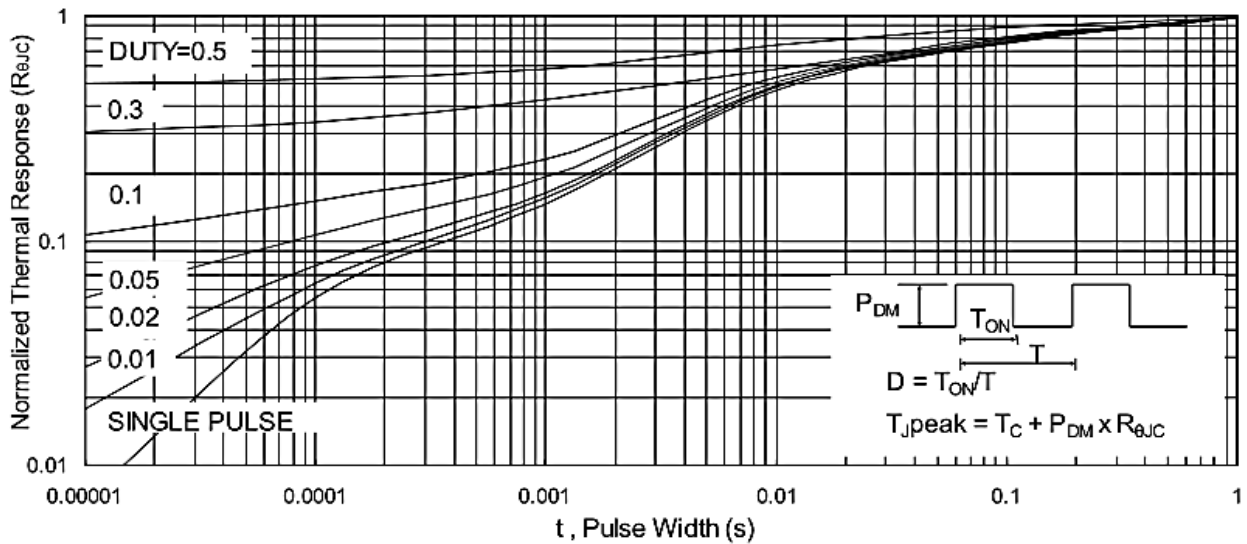
**Ratings and Characteristic Curves**



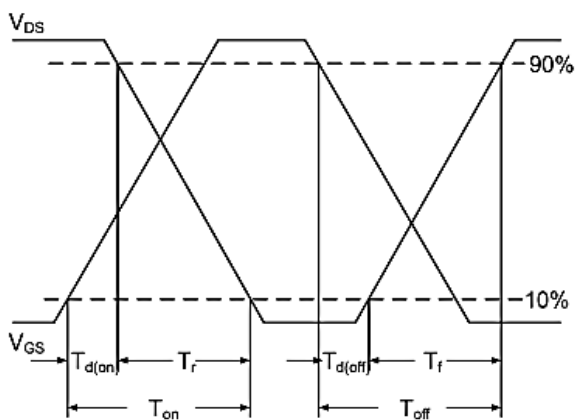
**Fig.7 Capacitance**



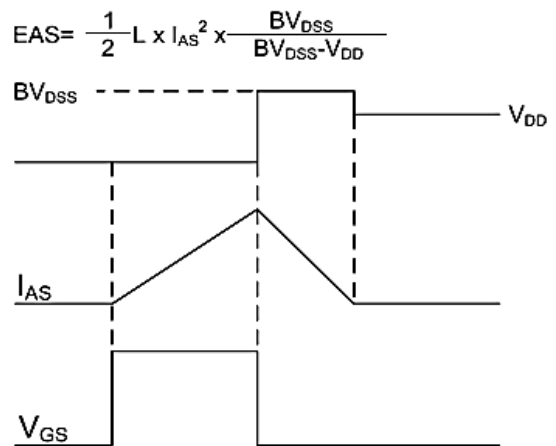
**Fig.8 Safe Operating Area**



**Fig.9 Normalized Maximum Transient Thermal Impedance**

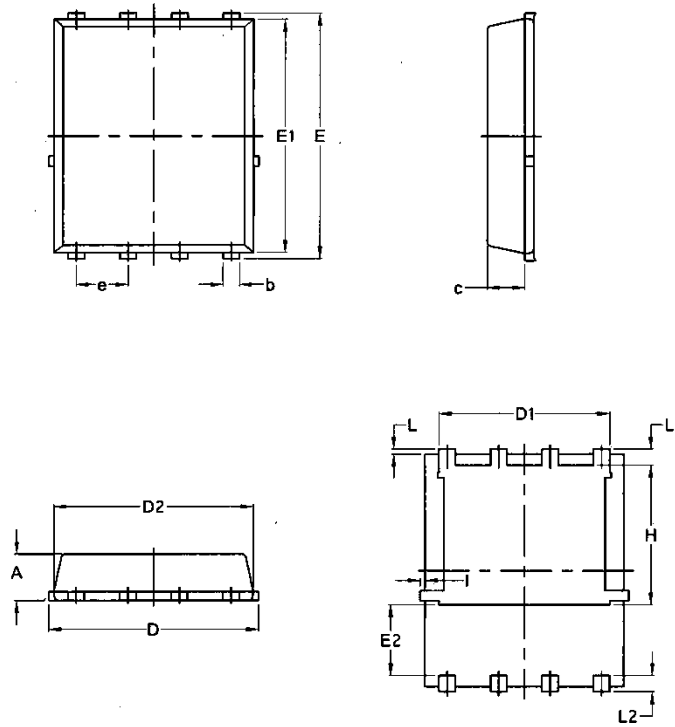


**Fig.10 Switching Time Waveform**



**Fig.11 Unclamped Inductive Switching Waveform**

**PDFN5\*6-8L**



Symbol	Common			
	mm		Inch	
	Min	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070